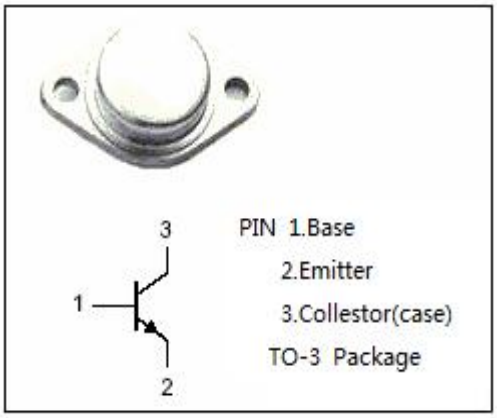
isc Silicon NPN Power Transistor — BU626A

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$ = 400V(Min.)
- Low Collector-Emitter Saturation Voltage-
  : $V_{CE(sat)}$ = 3.3V(Max.) @ I_C= 8A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

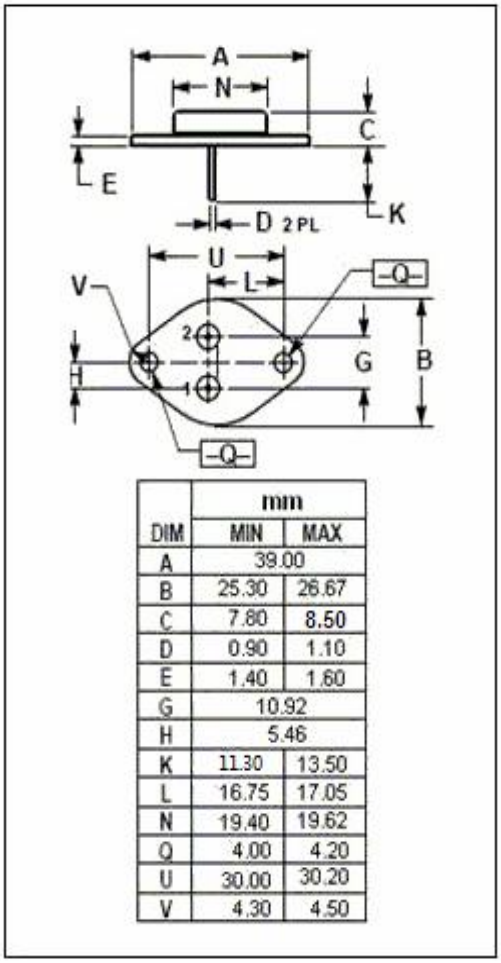
- Designed for use in power supply units of TV receivers.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1000	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	10	A
I_{CM}	Collector Current-Peak	15	A
P_C	Collector Power Dissipation @ T_C=25℃	100	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	1.5	℃/W



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 50mA; I_B= 0	400			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 10mA; I_C= 0	7			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 8A; I_B= 2.5A			3.3	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 8A; I_B= 2.5A			2.2	V
I_{CES}	Collector Cutoff Current	V_{CE}= 1000V; V_{BE}= 0			1.0	mA
h_{FE-1}	DC Current Gain	I_C= 10A; V_{CE}= 1.5V	10			
h_{FE-2}	DC Current Gain	I_C= 2.5A; V_{CE}= 10V	15			
f_T	Current-Gain—Bandwidth Product	I_C= 0.1A; V_{CE}= 10V	6			MHz
t_f	Fall Time	I_C= 8A; I_{B1}= -I_{B2}= 2.5A			1.0	μs